ON Semiconductor

Is Now

Onsemi

To learn more about onsemi[™], please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI: and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application is provided for uses as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi roducts for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs

1-of-8 Decoder/ Demultiplexer

High-Performance Silicon-Gate CMOS

The MC74HC138A is identical in pinout to the LS138. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC138A decodes a three-bit Address to one-of-eight active-low outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

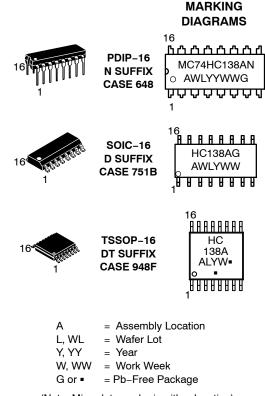
Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 100 FETs or 29 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

http://onsemi.com



(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

_			_
A0 [1•	16	□ v _{cc}
A1 🛛		15	1 Y0
A2 🛛	3	14	D Y1
CS2 [4	13] Y2
сѕз 🛛		12	D Y3
CS1 [6	11	D Y4
Y7 🛛	7	10	D Y5
GND [8	9	D Y6
-			-

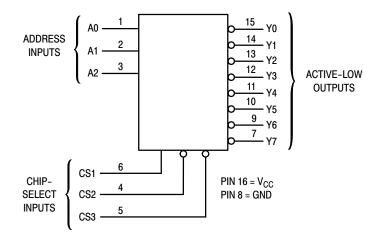


Figure 1. Pin Assignment

Figure 2. Logic Diagram

		-
FUN	CTION	_ E

		Inp	uts						Out	tput	s		
CS	1 CS2	CS3	A2	A1	A0	Y0	Y1	Y2	Y3	Y 4	Y5	Y6	Y7
X	Х	Н	Х	Х	Х	н	Н	Н	Н	Н	Н	Н	Н
X	Н	Х	Х	Х	Х	н	н	Н	Н	Н	Н	Н	Н
L	Х	Х	Х	Х	Х	н	Н	Н	Н	Н	Н	Н	Н
н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
н	L	L	L	L	Н	н	L	Н	Н	Н	Н	Н	Н
H	L	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
н	L	L	L	Н	Н	н	Н	Н	L	Н	Н	Н	Н
н	L	L	Н	L	L	н	Н	Н	Н	L	Н	Н	Н
H	L	L	н	L	Н	Н	Н	Н	Н	Н	L	Н	Н
н	L	L	н	н	L	н	н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	н	Н	Н	Н	Н	Н	Н	L

H = high level (steady state); L = low level (steady state); X = don't care

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC138ANG	PDIP-16 (Pb-Free)	500 Units / Rail
MC74HC138ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC138ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74HC138ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV74HC138ADR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel
NLV74HC138ADTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V_CC + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	– 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating – Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: $-7 \text{ mW/}^{\circ}\text{C}$ from 65° to 125°C

TSSOP Package: - 6.1 .W/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 2) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

			V _{cc}	Guara	nteed Limit		
Symbol	Parameter	Test Conditions	v	–55°C to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$	2.0	1.5	1.5	1.5	V
	Voltage	$ I_{out} \le 20 \ \mu A$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
VIL	Maximum Low-Level Input	$V_{out} = 0.1 V \text{ or } V_{CC} - 0.1 V$	2.0	0.5	0.5	0.5	V
	Voltage	$ I_{out} \le 20 \ \mu A$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output	V _{in} = V _{IH} or V _{IL}	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out} \le 20 \mu A$	4.5	4.4	4.4	4.4	
	_		6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH} \text{ or } V_{IL} I_{out} \le 2.4 \text{ mA}$	3.0	2.48	2.34	2.20	
		$ I_{out} \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.70	
		$ I_{out} \le 5.2 \text{ mA}$	6.0	5.48	5.34	5.20	
Vol	Maximum Low-Level Output	V _{in} = V _{IH} or V _{IL}	2.0	0.1	0.1	0.1	V
	Voltage	$ I_{out} \le 20 \mu A$	4.5	0.1	0.1	0.1	
	_		6.0	0.1	0.1	0.1	
		$V_{in} = V_{IH} \text{ or } V_{IL} I_{out} \le 2.4 \text{ mA}$	3.0	0.26	0.33	0.40	
		$ I_{out} \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.40	
		$ I_{out} \le 5.2 \text{ mA}$	6.0	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or GND}$ $I_{out} = 0 \ \mu A$	6.0	4	40	160	μA
		4		4			

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

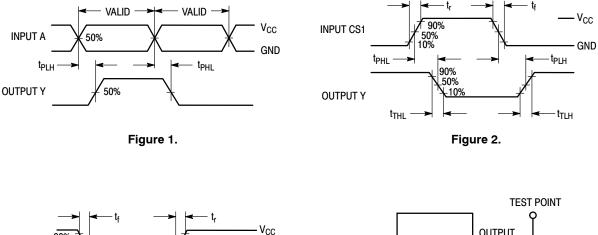
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

		V _{cc}	Guara			
Symbol	Parameter	V	–55°C to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} ,	Maximum Propagation Delay, Input A to Output Y	2.0	135	170	205	ns
t _{PHL}	(Figures 1 and 4)	3.0	90	125	165	
=		4.5	27	34	41	
		6.0	23	29	35	
t _{PLH} ,	Maximum Propagation Delay, CS1 to Output Y	2.0	110	140	165	ns
tPHL	(Figures 2 and 4)	3.0	85	100	125	
		4.5	22	28	33	
		6.0	19	24	28	
t _{PLH} ,	Maximum Propagation Delay, CS2 or CS3 to Output Y	2.0	120	150	180	ns
t _{PHL}	(Figures 3 and 4)	3.0	90	120	150	
		4.5	24	30	36	
		6.0	20	26	31	
t _{TLH} ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t _{THL}	(Figures 2 and 4)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Package)*	55	pF
* Llead to d	determine the not load dynamic power consumption: $P_{-} = C_{-} = V_{0} c_{0}^{2} f + 1$		

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

SWITCHING WAVEFORMS



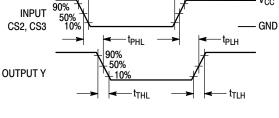
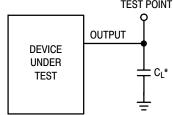


Figure 3.



*Includes all probe and jig capacitance

Figure 4. Test Circuit

PIN DESCRIPTIONS

ADDRESS INPUTS

A0, A1, A2 (Pins 1, 2, 3)

Address inputs. These inputs, when the chip is selected, determine which of the eight outputs is active-low.

CONTROL INPUTS CS1, CS2, CS3 (Pins 6, 4, 5)

Chip select inputs. For CS1 at a high level and CS2, CS3 at a low level, the chip is selected and the outputs follow the

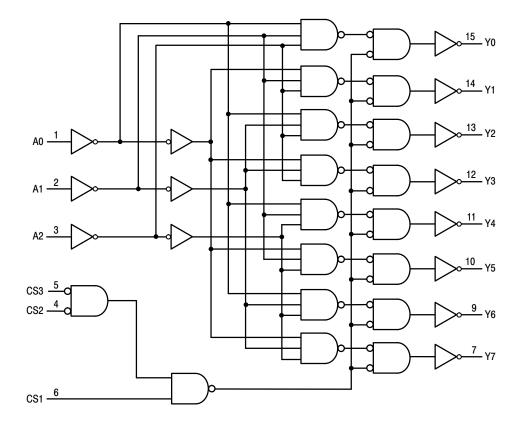
Address inputs. For any other combination of CS1, CS2, and CS3, the outputs are at a logic high.

OUTPUTS

Y0 - Y7 (Pins 15, 14, 13, 12, 11, 10, 9, 7)

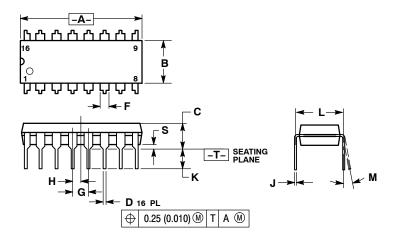
Active-low Decoded outputs. These outputs assume a low level when addressed and the chip is selected. These outputs remain high when not addressed or the chip is not selected.

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS

PDIP-16 CASE 648-08 ISSUE T

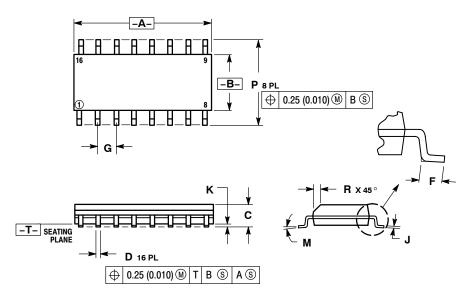


- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
н	0.050	BSC	1.27	BSC	
J	0.008	0.015	0.21	0.38	
К	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
М	0 °	10 °	0 °	10 °	
S	0.020	0.040	0.51	1.01	

PACKAGE DIMENSIONS

SOIC-16 CASE 751B-05 ISSUE K



NOTES:

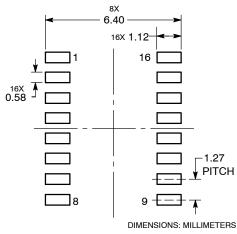
- NO LES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. MULTINGI D. PROTRUSION (C. 40.200) DED

4. 5.

MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	1.27 BSC) BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Ρ	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

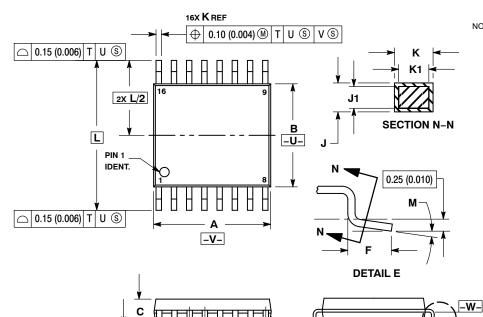
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-16 CASE 948F-01 **ISSUE B**



G

NOTES:

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS.

FLASH. PROTRUSIONS OR GATE BURRS.
MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

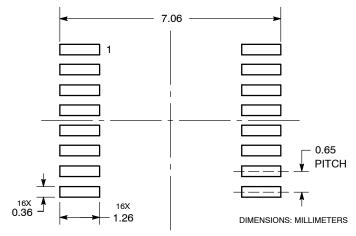
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
К	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L		40 BSC (BSC
Μ	0 °	8 °	0 °	8 °

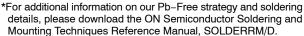
SOLDERING FOOTPRINT*

DETAIL E

-

Н





0.10 (0.004) -T- SEATING PLANE

D

ON Semiconductor and where registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent–Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC solutes on to convey any license under its patent rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC for any claims, damages, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for r

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Downloaded from Arrow.com.